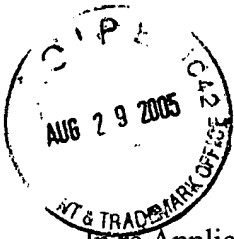


AF/11W



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:

Chris E. Barns et al.

Serial No.: 10/629,127

Filed: July 29, 2003

For: Preventing Silicide Formation at
the Gate Electrode in a Replacement
Metal Gate Technology

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Art Unit: 2822

Examiner: Khanh B. Duong

Docket: ITL.1016US
P16703

Assignee: Intel Corporation

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO FINAL REJECTION

Sir:

In response to the final rejection mailed August 8, 2005, please amend the above-referenced patent application as follows:

Date of Deposit: August 26, 2005

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Cynthia L. Hayden
Cynthia L. Hayden